

查询BCW66FR供应商

**SOT23 NPN SILICON PLANAR
MEDIUM POWER TRANSISTOR**

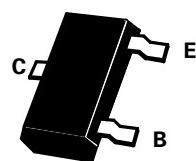
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PARTMARKING DETAILS -

BCW66F -	EF	BCW66FR -	7P
BCW66G -	EG	BCW66GR -	5T
BCW66H -	EH	BCW66HR -	7M

COMPLEMENTARY TYPE - BCW68

BCW66



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	800	mA
Peak Collector Current(10ms)	I_{CM}	1000	mA
Base Current	I_B	100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	°C

 **ZETEX**

BCW66

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	45			V	$I_{CEO}=10mA$
		$V_{(BR)CES}$	75			V	$I_C=10\mu A$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5			V	$I_{EBO}=10\mu A$
Collector-Emitter Cut-off Current		I_{CES}			20 20	nA μA	$V_{CES} = 45V$ $V_{CES} = 45V, T_{amb} = 150^\circ C$
Emitter-Base Cut-Off Current		I_{EBO}			20	nA	$V_{EBO} = 4V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			0.3 0.7	V V	$I_C=100mA, I_B = 10mA$ $I_C = 500mA, I_B = 50mA^*$
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			2	V	$I_C=500mA, I_B=50mA^*$
Static Forward Current Transfer	BCW66F	h_{FE}	75 100 35	160	250		$I_C = 10mA, V_{CE} = 1V$ $I_C = 100mA, V_{CE} = 1V^*$ $I_C = 500mA, V_{CE} = 2V^*$
	BCW66G	h_{FE}	110 160 60	250	400		$I_C = 10mA, V_{CE} = 1V$ $I_C = 100mA, V_{CE} = 1V^*$ $I_C = 500mA, V_{CE} = 2V^*$
	BCW66H	h_{FE}	180 250 100	350	630		$I_C = 10mA, V_{CE} = 1V$ $I_C = 100mA, V_{CE} = 1V^*$ $I_C = 500mA, V_{CE} = 2V^*$
Transition Frequency		f_T	100			MHz	$I_C = 20mA, V_{CE} = 10V$ $f = 100MHz$
Output Capacitance		C_{obo}		8	12	pF	$V_{CB} = 10V, f = 1MHz$
Input Capacitance		C_{ibo}			80	pF	$V_{EB} = 0.5V, f = 1MHz$
Noise Figure		N		2	10	dB	$I_C = 0.2mA, V_{CE} = 5V$ $R_G = 1k\Omega$
Switching times: Turn-On Time Turn-Off Time		t_{on} t_{off}			100 400	ns ns	$I_C = 150mA$ $I_{B1} = -I_{B2} = 15mA$ $R_L = 150\Omega$

Spice parameter data is available upon request for this device

*Measured under pulsed conditions.

